

UNR31A2

Silicon PNP epitaxial planar transistor

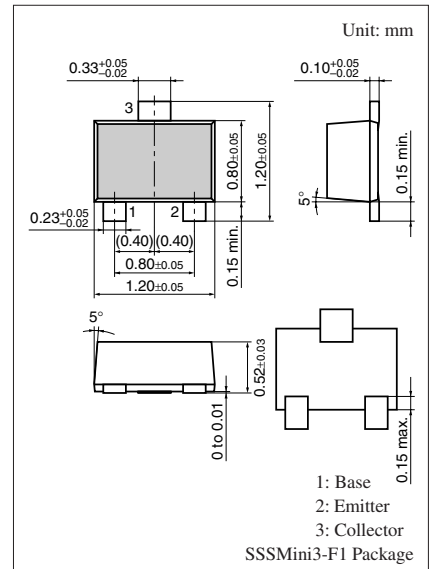
For digital circuits

■ Features

- Suitable for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

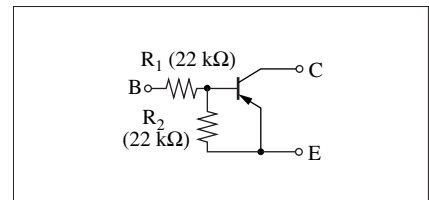
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-50	V
Collector-emitter voltage (Base open)	V_{CEO}	-50	V
Collector current	I_{C}	-80	mA
Total power dissipation	P_{T}	100	mW
Junction temperature	T_{j}	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$



Marking Symbol: CF

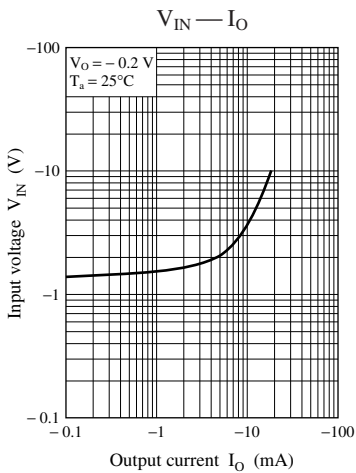
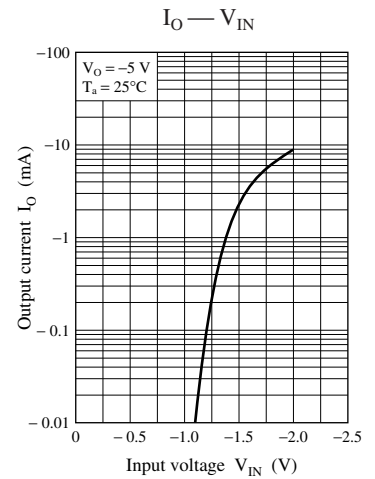
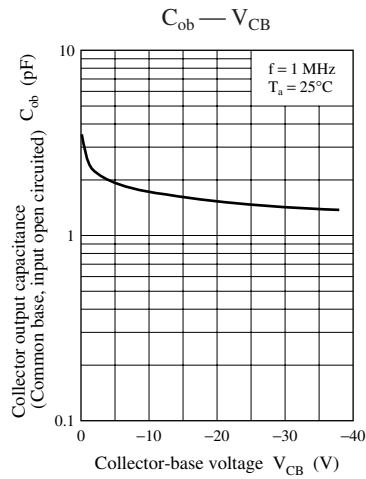
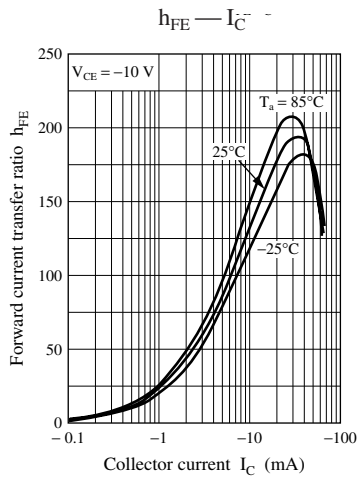
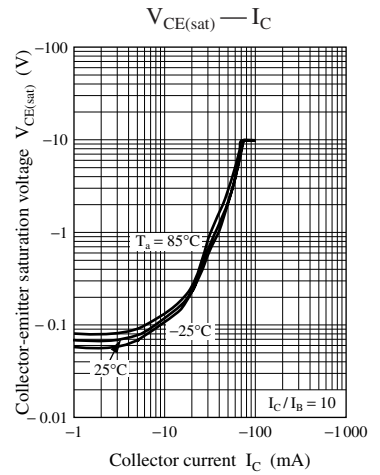
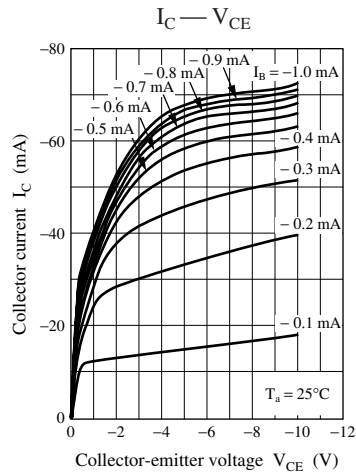
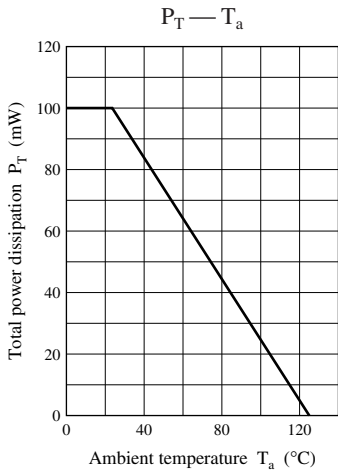
Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\text{C}} = -10 \mu\text{A}$, $I_{\text{E}} = 0$	-50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_{\text{C}} = -2 \text{ mA}$, $I_{\text{B}} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\text{CB}} = -50 \text{ V}$, $I_{\text{E}} = 0$			-0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{\text{CE}} = -50 \text{ V}$, $I_{\text{B}} = 0$			-0.5	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{\text{EB}} = -6 \text{ V}$, $I_{\text{C}} = 0$			-0.2	mA
Forward current transfer ratio	h_{FE}	$V_{\text{CE}} = -10 \text{ V}$, $I_{\text{C}} = -5 \text{ mA}$	60			—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -10 \text{ mA}$, $I_{\text{B}} = -0.3 \text{ mA}$			-0.25	V
Output voltage high-level	V_{OH}	$V_{\text{CC}} = -5 \text{ V}$, $V_{\text{B}} = -0.5 \text{ V}$, $R_{\text{L}} = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V_{OL}	$V_{\text{CC}} = -5 \text{ V}$, $V_{\text{B}} = -2.5 \text{ V}$, $R_{\text{L}} = 1 \text{ k}\Omega$			-0.2	V
Input resistance	R_{I}		-30%	22	+30%	$\text{k}\Omega$
Resistance ratio	$R_{\text{I}} / R_{\text{2}}$		0.8	1.0	1.2	—
Transition frequency	f_{T}	$V_{\text{CB}} = -10 \text{ V}$, $I_{\text{E}} = 1 \text{ mA}$, $f = 200 \text{ MHz}$		80		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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